

Nobuyuki Matsuki

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Fabrication of Lead Halide Perovskite Thin Films by Laser Alternate Deposition: Variation of Physical Properties with Layered Structure. , 2021, , .		0
2	(Invited) Halide Perovskite Thin Films via Alternate Laser Deposition: Change in the Physical Properties with the Layered Structures. ECS Meeting Abstracts, 2021, MA2021-02, 637-637.	0.0	0
3	Inter-Layer Solid-Phase Reaction in Halide Perovskite Fabricated via Alternate Laser Deposition. , 2020, , .		0
4	Interlayer Solid-Phase Reaction in Halide Perovskite Thin Films Fabricated Via Alternate Infrared Laser Deposition. ECS Meeting Abstracts, 2020, MA2020-02, 1860-1860.	0.0	0
5	<i>(Invited)</i> A Novel Optical Characterization of a-Si:H/c-Si Interface Microstructures Based on Data of Positron Annihilation Spectroscopy. ECS Transactions, 2019, 92, 21-24.	0.5	0
6	(Invited) A Novel Optical Characterization of a-Si:H/c-Si Interface Microstructures Based on Data of Positron Annihilation Spectroscopy. ECS Meeting Abstracts, 2019, , .	0.0	0
7	Combinatorial screening of halide perovskite thin films and solar cells by mask-defined IR laser molecular beam epitaxy. Science and Technology of Advanced Materials, 2017, 18, 307-315.	6.1	26
8	Impact of sputter-induced ion bombardment at the heterointerfaces of a-Si:H/c-Si solar cells with double-layered In₂O₃:Sn structures. Japanese Journal of Applied Physics, 2015, 54, 08KD09.	1.5	6
9	Characterization of a-Si:H thin layers incorporated into textured a-Si:H/c-Si solar cell structures by spectroscopic ellipsometry using a tilt-angle optical configuration. Thin Solid Films, 2014, 569, 64-69.	1.8	7
10	Nondestructive characterization of textured a-Si:H/c-Si heterojunction solar cell structures with nanometer-scale a-Si:H and In2O3:Sn layers by spectroscopic ellipsometry. Journal of Applied Physics, 2013, 114, .	2.5	9
11	Local network structure of a-SiC:H and its correlation with dielectric function. Journal of Applied Physics, 2013, 114, 233513.	2.5	8
12	Complete parameterization of the dielectric function of microcrystalline silicon fabricated by plasma-enhanced chemical vapor deposition. Journal of Applied Physics, 2012, 111, .	2.5	25
13	Reply to "Comment on 'Photovoltaic Action in Polyaniline/n-GaN Schottky Diodes'" Applied Physics Express, 2012, 5, 029102.	2.4	0
14	Transparent Conducting Polymer/Nitride Semiconductor Heterojunction Solar Cells. , 2011, , .		2
15	ï€-Conjugated polymer/GaN Schottky solar cells. Solar Energy Materials and Solar Cells, 2011, 95, 284-287.	6.2	21
16	Photocapacitance spectroscopy study of deep-level defects in freestanding n-GaN substrates using transparent conductive polymer Schottky contacts. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	1.2	6
17	Deep-Level Characterization of Free-Standing HVPE-grown GaN Substrates Using Transparent Conductive Polyaniline Schottky Contacts. Materials Research Society Symposia Proceedings, 2011, 1309, 97.	0.1	0
18	Deep-Level Characterization of n-GaN Epitaxial Layers Using Transparent Conductive Polyaniline Schottky Contacts. Japanese Journal of Applied Physics, 2011, 50, 01AD02.	1.5	7

#	ARTICLE	IF	CITATIONS
19	Deep-Level Characterization of n-GaN Epitaxial Layers Using Transparent Conductive Polyaniline Schottky Contacts. Japanese Journal of Applied Physics, 2011, 50, 01AD02.	1.5	2
20	Anomalous capacitance-voltage characteristics of Pt-AlGaIn/GaN Schottky diodes exposed to hydrogen. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1928-1930.	0.8	9
21	Electrical characterization of n-GaN epilayers using transparent polyaniline Schottky contacts. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2007-2009.	0.8	4
22	Ellipsometry Characterization of Hydrogenated Amorphous Silicon Layers Formed on Textured Crystalline Silicon Substrates. Applied Physics Express, 2010, 3, 116604.	2.4	11
23	HETEROINTERFACE PROPERTIES OF NOVEL HYBRID SOLAR CELLS CONSISTING OF TRANSPARENT CONDUCTIVE POLYMERS AND III-NITRIDE SEMICONDUCTOR. Journal of Nonlinear Optical Physics and Materials, 2010, 19, 703-711.	1.8	5
24	Photovoltaic Action in Polyaniline/n-GaN Schottky Diodes. Applied Physics Express, 2009, 2, 092201.	2.4	18
25	Low-frequency capacitance-voltage study of hydrogen interaction with Pt-AlGaIn/GaN Schottky barrier diodes. Physica Status Solidi - Rapid Research Letters, 2009, 3, 266-268.	2.4	6
26	Direct observation of the electrical activity of coincidence-site lattice boundaries in location-controlled silicon islands using scanning spread resistance microscopy. Journal of the Society for Information Display, 2009, 17, 293-297.	2.1	1
27	Investigation of local electrical properties of coincidence-site-lattice boundaries in location-controlled silicon islands using scanning capacitance microscopy. Applied Physics Letters, 2008, 93, 062102.	3.3	18
28	Unusual hydrogen distribution and its change in hydrogenated amorphous silicon prepared using bias electric-field molecular beam deposition. Applied Physics Letters, 2006, 89, 011909.	3.3	0
29	Characteristics of AlN/Ni(111) Heterostructures and their Application to Epitaxial Growth of GaN. Japanese Journal of Applied Physics, 2006, 45, L396-L398.	1.5	5
30	Heteroepitaxial growth of gallium nitride on muscovite mica plates by pulsed laser deposition. Solid State Communications, 2005, 136, 338-341.	1.9	9
31	Field-effect a-Si:H solar cells with transparent conductive oxide comb-shaped electrodes. Thin Solid Films, 2005, 486, 210-213.	1.8	5
32	Novel network control in hydrogenated amorphous silicon by molecular beam deposition method. Journal of Non-Crystalline Solids, 2004, 338-340, 382-385.	3.1	1
33	Concept and performance of a field-effect amorphous silicon solar cell. Semiconductor Science and Technology, 2004, 19, 61-64.	2.0	22
34	Improved performance of amorphous silicon thin film transistors by cyanide treatment. Applied Physics Letters, 2001, 78, 751-753.	3.3	5
35	In-plane structure of an arsenic-adsorbed Si(001) surface probed with grazing-angle x-ray standing waves. Physical Review B, 1999, 60, 15546-15549.	3.2	5
36	Device simulation and fabrication of field effect solar cells. Bulletin of Materials Science, 1999, 22, 729-733.	1.7	6